

General Description

Maxim's redesigned DG444/DG445 analog switches now feature on-resistance matching (4 Ω max) between switches and guaranteed on-resistance flatness over the signal range (9 Ω max). These low on-resistance switches conduct equally well in either direction. They guarantee low charge injection (10pC max), low power consumption (35µW max), and an ESD tolerance of 2000V minimum per Method 3015.7. The new design offers lower off leakage current over temperature (less than 5nA at +85°C).

The DG444/DG445 are quad, single-pole/single-throw (SPST) analog switches. The DG444 has 4 normally closed switches and the DG445 has 4 normally open switches. Switching times are less than 250ns for toN and less than 70ns for toFF. Operation is from a single +10V to +30V supply, or bipolar ±4.5V to ±20V supplies. Maxim's improved DG444/DG445 continue to be fabricated with a 44V silicon-gate process.

Applications

Sample-and-Hold Circuits	Communication Systems
Test Equipment	Battery-Operated Systems
Heads-Up Displays	PBX, PABX
Guidance and Control Syste	ems Audio Signal Routing
Military Radios	Modems/Faxes

_New Features

- ♦ Plug-In Upgrades for Industry-Standard DG444/DG445
- ♦ Improved ron Match Between Channels (4Ω max)
- ♦ Guaranteed rFLAT(ON) Over Signal Range (9Ω max)
- **♦** Improved Charge Injection (10pC max)
- Improved Off Leakage Current Over Temperature (<5nA at +85°C)
- Withstand Electrostatic Discharge (2000V min) per Method 3015.7

Existing Features

- ♦ Low rds(ON) (85 Ω max)
- ♦ Single-Supply Operation +10V to +30V Bipolar-Supply Operation ±4.5V to ±20V
- **♦ Low Power Consumption (35µW max)**
- ♦ Rail-to-Rail Signal Handling
- **♦ TTL/CMOS-Logic Compatible**

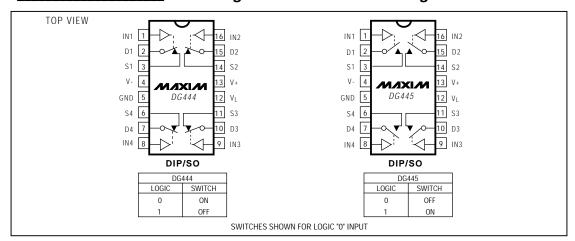
_Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
DG444CJ	0°C to +70°C	16 Plastic DIP
DG444DY	0°C to +70°C	16 Narrow SO
DG444C/D	0°C to +70°C	Dice*
DG444DJ	-40°C to +85°C	16 Plastic DIP
DG444DY	-40°C to +85°C	16 Narrow SO

Ordering Information continued at end of data sheet.

* Contact factory for dice specifications.

Pin Configurations/Functional Diagrams/Truth Tables



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ABSOLUTE MAXIMUM RATINGS

Dissipation (T _A = +70°C)
(derate 10.53mW/°C above +70°C) 842mW
(derate 8.70mW/°C above +70°C)696mW
ture Ranges
0°C to +70°C
40°C to +85°C
re Range65°C to +150°C
(soldering, 10sec)+300°C
)

Note 1: Signals on S, D, or IN exceeding V+ or V- are clamped by internal diodes. Limit forward current to maximum current rating.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS—Dual Supplies

 $(V+=15V, V-=-15V, V_L=5V, GND=0V, V_{INH}=2.4V, V_{INL}=0.8V, T_A=T_{MIN}$ to T_{MAX} , unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP (Note 2)	MAX	UNITS
SWITCH							•
Analog Signal Range	V _{ANALOG}	(Note 3)		-15		15	V
Drain-Source	rds(on)	V+ = 13.5V, V- = -13.5V, $VD = \pm 8.5V.$	T _A = +25°C		50	85	Ω
On-Resistance	1D3(ON)	Is = -10mA	TA = TMIN to TMAX			100	32
On-Resistance Match	Δr _{DS(ON)}	V _D = ±10V,	T _A = +25°C			4	Ω
Between Channels (Note 4)	AIDS(ON)	Is = -10mA	TA = TMIN to TMAX			5	52
On-Resistance Flatness (Note 4)	rflat(ON)	$V_D = \pm 5V$, $I_S = -10\text{mA}$	T _A = +25°C			9	Ω
			$T_A = T_{MIN}$ to T_{MAX}			15	
Source Leakage Current (Note 5)	Is(OFF)	V + = 16.5V, V - = -16.5V, $V_D = \pm 15.5V,$ $V_S = \mp 15.5V$	T _A = +25°C	-0.50	0.01	0.50	nA
			TA = TMIN to TMAX	-5		5	
Drain-Off Leakage Current	$V+ = 16.5V, V- = -16.5V,$ $VD = \pm 15.5V.$	T _A = +25°C	-0.50	0.01	0.50	- nA	
(Note 5)	ID(OFF)	$V_S = \pm 15.5V$, $V_S = \pm 15.5V$ $T_A = T_{MIN}$ to T_{MAX}	-5		5		
Drain-On Leakage Current (Note 5)	ID(ON)	V+ = 16.5V, V- = -16.5V, $VD = \pm 15.5V.$	T _A = +25°C	-0.50	0.08	0.50	nA
	I _{S(ON)}	$V_D = \pm 15.5V$, $V_S = \pm 15.5V$	$T_A = T_{MIN}$ to T_{MAX}	-10		10	IIA
INPUT							
Input Current with Input Voltage High	linh	V _{IN} = 2.4V, all others = 0).8V	-0.5	-0.00001	0.5	μA
Input Current with Input Voltage Low	linl	V _{IN} = 0.8V, all others = 2	4V	-0.5	-0.00001	0.5	μA

ELECTRICAL CHARACTERISTICS—Dual Supplies (continued) (V+ = 15V, V- = -15V, V_L = 5V, GND = 0V, V_{INH} = 2.4V, V_{INL} = 0.8V, T_{A} = T_{MIN} to T_{MAX} , unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP (Note 2)	MAX	UNITS	
SUPPLY								
Power-Supply Range	V+, V-			±4.5		±20.0	V	
Positive Supply Current	1+	All channels on or off, V+ = 16.5V, V- = -16.5V,	T _A = +25°C	-1	0.001	1	μA	
Toshive Supply Current	17	V _{IN} = 0V or 5V	TA = TMIN to TMAX	-5		5	μΑ	
Negative Supply Current	-	All channels on or off, V+ = 16.5V, V- = -16.5V,	T _A = +25°C	-1	-0.0001	1		
Negative Supply Current	1-	V _{IN} = 0V or 5V	$T_A = T_{MIN}$ to T_{MAX}	-5		5	μA	
Lagia Cupply Current	1.	All channels on or off, V+ = 16.5V, V- = -16.5V.	T _A = +25°C	-1	0.001	1	_	
Logic Supply Current	lL l	V+ = 16.5V, V- = -16.5V, V _{IN} = 0V or 5V	TA = TMIN to TMAX	-5		5	- μΑ	
	IGND	All channels on or off, V+ = 16.5V, V- = -16.5V, V _{IN} = 0V or 5V	T _A = +25°C	-1	-0.0001	1	- µА	
Ground Current			TA = TMIN to TMAX	-5		5		
DYNAMIC				ı	-			
Turn-On Time	ton	$V_S = \pm 10V$, Figure 2	T _A = +25°C		150	250	ns	
Turn-Off Time toff	torr	DG444, V _S = ±10V, Figure 2	T _A = +25°C		90	120	ns	
	IOFF	DG445, V _S = ±10V, Figure 2	T _A = +25°C		110	170	ns	
Charge Injection (Note 3)	Q	$C_L = 1nF$, $V_{GEN} = 0V$, $R_{GEN} = 0\Omega$, Figure 3	T _A = +25°C		5	10	рС	
Off-Isolation Rejection Ratio (Note 6)	OIRR	$R_L = 50\Omega$, $C_L = 5pF$, $f = 1MHz$, Figure 4	T _A = +25°C		60		dB	
Crosstalk (Note 7)		$R_L - 50\Omega$, $C_L = 5pF$, $f = 1MHz$, Figure 5	T _A = +25°C		100		dB	
Source-Off Capacitance	Cs(off)	f = 1MHz, Figure 6	T _A = +25°C		4		pF	
Drain-Off Capacitance	C _D (OFF)	$f = 1MHz$, Figure 6 $T_A = +25$ °C			4		pF	
Source-On Capacitance	Cs(ON)	f = 1MHz, Figure 7	T _A = +25°C		16		pF	
Drain-On Capacitance	C _D (ON)	f = 1MHz, Figure 7	T _A = +25°C		16		pF	

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ELECTRICAL CHARACTERISTICS—Single Supply

 $(V + = 12V, V - = 0V, V_L = 5V, GND = 0V, V_{INH} = 2.4V, V_{INL} = 0.8V, T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS			MIN	TYP (Note 2)	MAX	UNITS
SWITCH								
Analog Signal Range	V _{ANALOG}	(Note 3)			0		12	V
Drain-Source	EDC(ON)	V+ = 10.8V, V _L = 5.25V, V _D = 3V, 8V, I _S = -10mA T _A = +25°C T _A = +25°C		- +25°C		100	160	Ω
On-Resistance	rDS(ON)			TMIN to TMAX			200	1 12
SUPPLY			•					
Power-Supply Range	V+, V-				10.8		24.0	V
Power-Supply Current	I+	All channels on or off,		$T_A = +25^{\circ}C$	-1	0.001	1	μА
		V _{IN} = 0V or 5V		TA = TMIN to TMAX	-5		5	
Negative Supply Current I-		All channels on or off, V _{IN} = 0V or 5V		T _A = +25°C	-1	-0.0001	1	μΑ
	1-			$T_A = T_{MIN}$ to T_{MAX}	-5		5	
Logic Supply Current	1	All channels on or off, TA		$T_A = +25^{\circ}C$	-1	0.001	1	μΑ
Logic Supply Current IL		$V_{IN} = 0V \text{ or } 5V$ $T_A = T_M$		$T_A = T_{MIN}$ to T_{MAX}	-5		5	- μΑ
Ground Current IGND	ICNID	All channels on or off, $T_A = +25^{\circ}C$ $V_{IN} = 0V \text{ or } 5V$ $T_A = T_{MIN} \text{ to}$		$T_A = +25^{\circ}C$	-1	-0.0001	1	μА
	IGND			$T_A = T_{MIN}$ to T_{MAX}	-5		5	μΑ
DYNAMIC								
Turn-On Time	ton	V _S = 8V, Figure 2		$T_A = +25^{\circ}C$		300	400	ns
Turn-Off Time	t _{OFF}	V _S = 8V, Figure 2		T _A = +25°C		60	200	ns
Charge Injection (Note 3)	Q	$C_L = 1nF$, $V_{GEN} = 0V$, $R_{GEN} = 0\Omega$, Figure 3 $T_A = +25^{\circ}C$			5	10	рС	

Note 2: Typical values are for design aid only, are not guaranteed and are not subject to production testing. The algebraic convention, where the most negative value is a minimum and the most positive value a maximum, is used in this data sheet.

Note 3: Guaranteed by design.

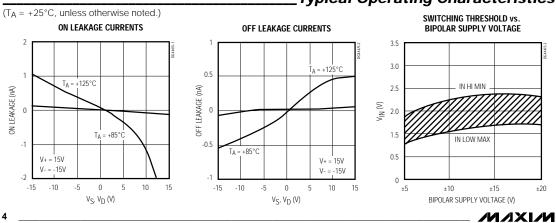
Note 4: On-resistance match between channels and flatness are guaranteed only with bipolar-supply operation. Flatness is defined as the difference between the maximum and the minimum value of on-resistance as measured at the extremes of the speci-

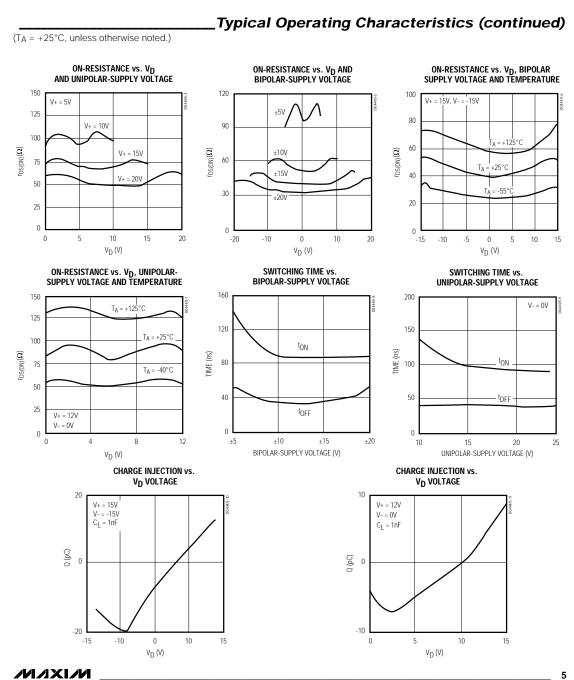
Note 5: Leakage parameters Is(OFF), ID(ON), and IS(ON), are100% tested at the maximum rated hot temperature and guaranteed at +25°C.

Note 6: Off-Isolation Rejection Ratio = 20log (VD/VS), VD = output, VS = input to off switch.

Note 7: Between any two switches.

Typical Operating Characteristics





Pin Description

PIN	NAME	FUNCTION	
1, 16, 9, 8	IN1-IN4	Logic Control Inputs	
2, 15, 10, 7	D1-D4	Drain Outputs	
3, 14, 11, 6	S1-S4	Source Outputs	
4	V-	Negative Supply-Voltage Input	
5	GND	Ground	
12	VL	Logic Supply-Voltage Input	
13	V+	Positive Supply-Voltage Input— connected to substrate	

Applications Information, General Operation

- 1. Switches are open when power is off.
- 2. IN, D, and S should not exceed V+ or V-, even with the power off.
- 3. Switch leakage is from each analog switch terminal to V+ or V-, not to other switch terminals.

Operation with Supply Voltages Other Than ±15V

Using supply voltages other than $\pm 15V$ will reduce the analog signal range. The DG444/DG445 switches operate with $\pm 4.5V$ to $\pm 20V$ bipolar supplies or with a +10V to +30V single supply: connect V- to 0V when operating with a single supply. Also, all device types can operate with unbalanced supplies such as +24V and -5V. V_L must be connected to +5V to be TTL compatible, or to V+ for CMOS-logic level inputs. The *Typical Operating*

Characteristics graphs show typical on-resistance with $\pm 20V$, $\pm 15V$, $\pm 10V$, and $\pm 5V$ supplies. (Switching times increase by a factor of two or more for operation at $\pm 5V$.)

Overvoltage Protection

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings may cause permanent damage to the devices. Always sequence V+ on first, followed by V_L , V-, and logic inputs. If power-supply sequencing is not possible, add two small, external signal diodes in series with supply pins for overvoltage protection (Figure 1). Adding diodes reduces the analog signal range to 1V below V+ and 1V above V-, but low switch resistance and low leakage characteristics are unaffected. Device operation is unchanged, and the difference between V+ and V-should not exceed +44V.

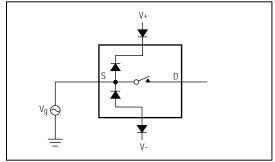


Figure 1. Overvoltage Protection Using External Blocking Diodes

Timing Diagrams/Test Circuits

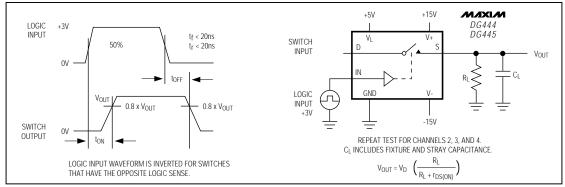


Figure 2. Switching Time

Timing Diagrams/Test Circuits (continued)

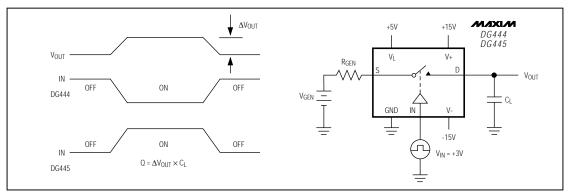


Figure 3. Charge Injection

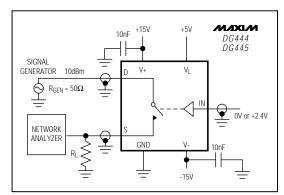


Figure 4. Off-Isolation Rejection Ratio

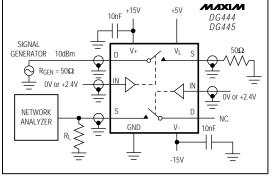


Figure 5. Crosstalk

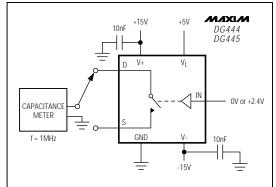


Figure 6. Source/Drain-Off Capacitance

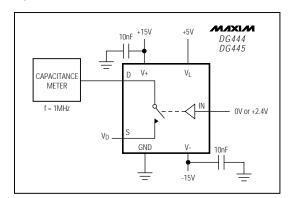


Figure 7. Source/Drain-On Capacitance

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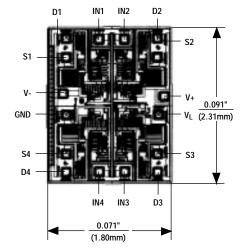
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_Ordering Information (continued)

PART	TEMP. RANGE	PIN-PACKAGE
DG445CJ	0°C to +70°C	16 Plastic DIP
DG445CY	0°C to +70°C	16 Narrow SO
DG445C/D	0°C to +70°C	Dice*
DG445DJ	-40°C to +85°C	16 Plastic DIP
DG445DY	-40°C to +85°C	16 Narrow SO

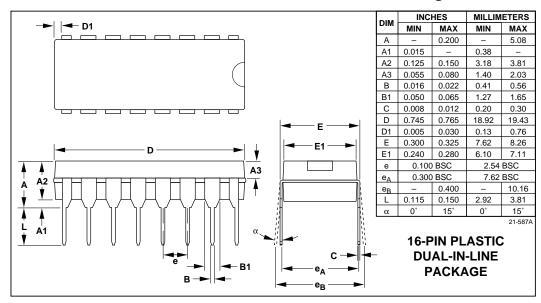
^{*} Contact factory for dice specifications.

__Chip Topography



TRANSISTOR COUNT: 126 SUBSTRATE CONNECTED TO V+

Package Information



Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.

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